

ABSTRACT OF THE DISCLOSURE

In a method of writing data in a nonvolatile memory device including a plurality of cell strings, each of the plurality of cell strings includes a plurality of memory cells disposed in a vertical direction. A program target page is divided into a plurality of subpages. The program target page is connected to one of a plurality of wordlines. Each of the plurality of subpages includes memory cells that are physically spaced apart from one another. A program operation is sequentially performed on the plurality of subpages. A program verification operation is performed on the program target page including the plurality of subpages at a time.

10

FIG. 1